

# IGBT - Power, Co-PAK N-Channel, Field Stop VII (FS7), Non-SCR, TO247-3L 1200 V, 1.7 V, 100 A FGY100T120SWD

## Description

Using the novel field stop 7th generation IGBT technology and the Gen7 Diode in TO247 3-lead package, FGY100T120SWD offers the optimum performance with low switching and conduction losses for high-efficiency operations in various applications like Solar, UPS, and ESS.

## Features

- Maximum Junction Temperature  $T_J = 175^\circ\text{C}$
- Positive Temperature Coefficient for Easy Parallel Operation
- High Current Capability
- Smooth and Optimized Switching
- Low Switching Loss
- RoHS Compliant

## Applications

- Boost and Inverter in Solar System
- UPS
- Energy Storage System

## MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

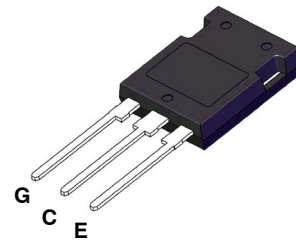
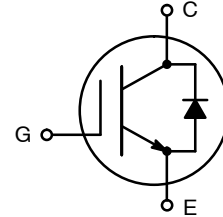
Parameter	Symbol	Value	Unit	
Collector-to-Emitter Voltage	$V_{CES}$	1200	V	
Gate-to-Emitter Voltage	$V_{GES}$	$\pm 20$	V	
Transient Gate-to-Emitter Voltage		$\pm 30$	V	
Collector Current	$I_C$	$T_C = 25^\circ\text{C}$ (Note 1)	200	A
		$T_C = 100^\circ\text{C}$	100	
Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	866	W
		$T_C = 100^\circ\text{C}$	433	
Pulsed Collector Current	$I_{CM}$	400	A	
Diode Forward Current	$I_F$	$T_C = 25^\circ\text{C}$	200	A
		$T_C = 100^\circ\text{C}$	100	
Pulsed Diode Maximum Forward Current	$I_{FM}$	400	A	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$	
Lead Temperature for Soldering Purposes	$T_L$	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Value limit by bond wire
2. Repetitive rating: Pulse width limited by max. Junction temperature

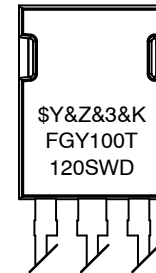
$BV_{CES}$	$V_{CE(SAT)}$	$I_C$
1200 V	1.7 V	100 A

## PIN CONNECTIONS



TO247-3LD  
CASE 340CD

## MARKING DIAGRAM



- \$Y = onsemi Logo
- &Z = Assembly Plant Code
- &3 = 3-Digit Date Code
- &K = 2-Digit Lot Traceability Code
- FGY100T120SWD = Specific Device code

## ORDERING INFORMATION

Device	Package	Shipping
FGY100T120SWD	TO-247-3LD (Pb-Free)	30 Units / Tube

# FGY100T120SWD

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case for IGBT	$R_{\theta JC}$	0.17	°C/W
Thermal Resistance, Junction-to-Case for Diode		0.29	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS OF IGBT ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE} = 0\text{ V}, I_C = 5\text{ mA}$	1200			V
Collector-to-Emitter Breakdown Voltage Temperature Coefficient	$\Delta BV_{CES} / \Delta T_J$			1222		mV/°C
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$			40	μA
Gate-to-Emitter Leakage Current	$I_{GES}$	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$			±400	nA

### ON CHARACTERISTICS

Gate Threshold Voltage	$V_{GE(TH)}$	$V_{GE} = V_{CE}, I_C = 100\text{ mA}$	5.6	6.55	7.4	V
Collector-to-Emitter Saturation Voltage	$V_{CE(SAT)}$	$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 25^\circ\text{C}$	1.35	1.69	2.0	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 175^\circ\text{C}$		2.26		

### DYNAMIC CHARACTERISTICS

Input Capacitance	$C_{IES}$	$V_{GE} = 0\text{ V}, V_{CE} = 30\text{ V}, f = 1\text{ MHz}$		8489		pF
Output Capacitance	$C_{OES}$			320		
Reverse Transfer Capacitance	$C_{RES}$			41.4		
Total Gate Charge	$Q_G$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 100\text{ A}$		284		nC
Gate-to-Emitter Charge	$Q_{GE}$			72.4		
Gate-to-Collector Charge	$Q_{GC}$			101		

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 50\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$		46.4		ns	
Turn-Off Delay Time	$t_{d(off)}$			209.6			
Rise Time	$t_r$			30.4			
Fall Time	$t_f$			58			
Turn-On Switching Loss	$E_{on}$			3.1			mJ
Turn-Off Switching Loss	$E_{off}$			1.6			
Total Switching Loss	$E_{ts}$			4.7			
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 0/15\text{ V}, I_C = 100\text{ A}, R_G = 4.7\ \Omega, T_J = 25^\circ\text{C}$		46.4		ns	
Turn-Off Delay Time	$t_{d(off)}$			168			
Rise Time	$t_r$			72			
Fall Time	$t_f$			51.2			
Turn-On Switching Loss	$E_{on}$			8.1			mJ
Turn-Off Switching Loss	$E_{off}$			2.8			
Total Switching Loss	$E_{ts}$			10.9			

# FGY100T120SWD

## ELECTRICAL CHARACTERISTICS OF IGBT ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GE} = 0/15\text{ V}, I_C = 50\text{ A}, V_{CE} = 600\text{ V}, R_G = 4.7\ \Omega, T_J = 175^\circ\text{C}$		38.4		ns
Turn-Off Delay Time	$t_{d(off)}$			244.8		
Rise Time	$t_r$			28.8		
Fall Time	$t_f$			92.8		
Turn-On Switching Loss	$E_{on}$			4.9		mJ
Turn-Off Switching Loss	$E_{off}$			2.4		
Total Switching Loss	$E_{ts}$			7.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GE} = 0/15\text{ V}, I_C = 100\text{ A}, V_{CE} = 600\text{ V}, R_G = 4.7\ \Omega, T_J = 175^\circ\text{C}$		41.6		ns
Turn-Off Delay Time	$t_{d(off)}$			196.8		
Rise Time	$t_r$			64		
Fall Time	$t_f$			76.8		
Turn-On Switching Loss	$E_{on}$			11.3		mJ
Turn-Off Switching Loss	$E_{off}$			3.9		
Total Switching Loss	$E_{ts}$			15.2		

### DIODE CHARACTERISTICS

Forward Voltage	$V_F$	$I_F = 100\text{ A}, T_J = 25^\circ\text{C}$	1.62	1.82	2.22	V
		$I_F = 100\text{ A}, T_J = 175^\circ\text{C}$		1.87		

### DIODE SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 50\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		152		ns
Reverse Recovery Charge	$Q_{rr}$			2977		nC
Reverse Recovery Energy	$E_{rec}$			0.9		mJ
Peak Reverse Recovery Current	$I_{RRM}$			39		A
Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 100\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$		261		ns
Reverse Recovery Charge	$Q_{rr}$			5636		nC
Reverse Recovery Energy	$E_{rec}$			1.8		mJ
Peak Reverse Recovery Current	$I_{RRM}$			43		A
Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 50\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$		192		ns
Reverse Recovery Charge	$Q_{rr}$			5275		nC
Reverse Recovery Energy	$E_{rec}$			1.6		mJ
Peak Reverse Recovery Current	$I_{RRM}$			55		A
Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 100\text{ A}, di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$		358		ns
Reverse Recovery Charge	$Q_{rr}$			10858		nC
Reverse Recovery Energy	$E_{rec}$			3.6		mJ
Peak Reverse Recovery Current	$I_{RRM}$			61		A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# FGY100T120SWD

## TYPICAL CHARACTERISTICS

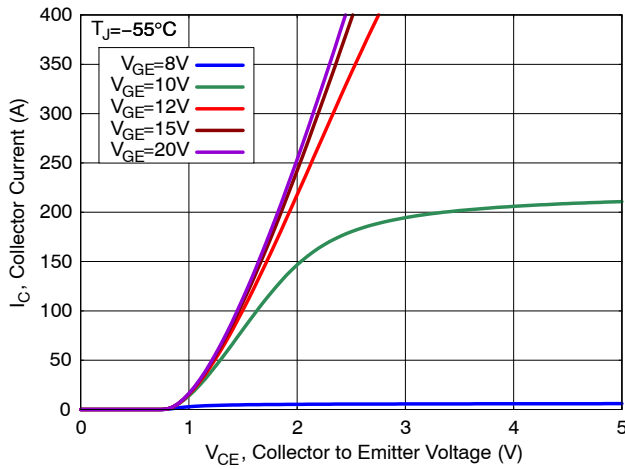


Figure 1. Output Characteristics

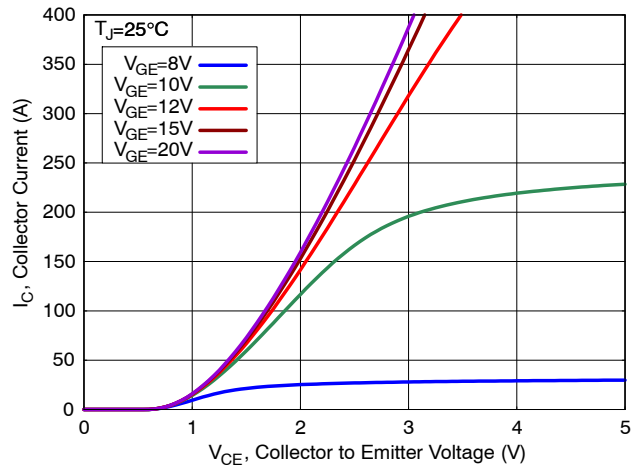


Figure 2. Output Characteristics

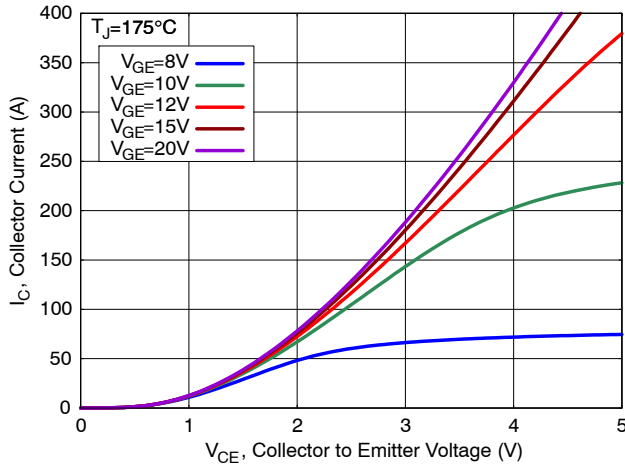


Figure 3. Output Characteristics

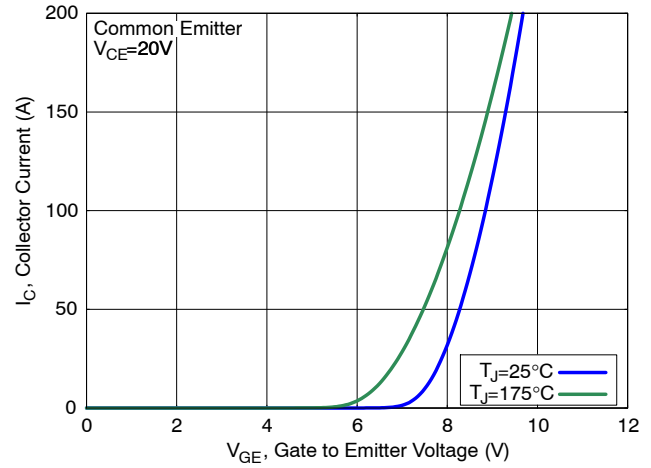


Figure 4. Transfer Characteristics

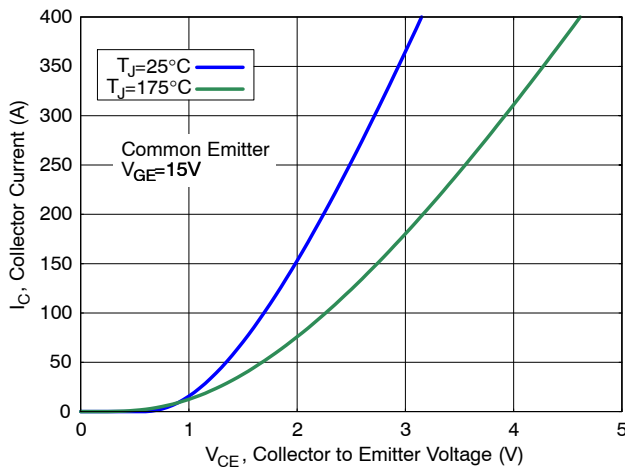


Figure 5. Saturation Characteristics

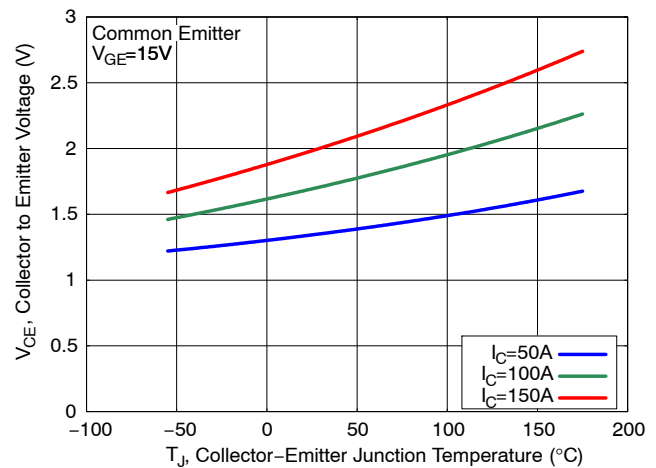


Figure 6. Saturation Voltage vs. Junction Temperature

# FGY100T120SWD

## TYPICAL CHARACTERISTICS

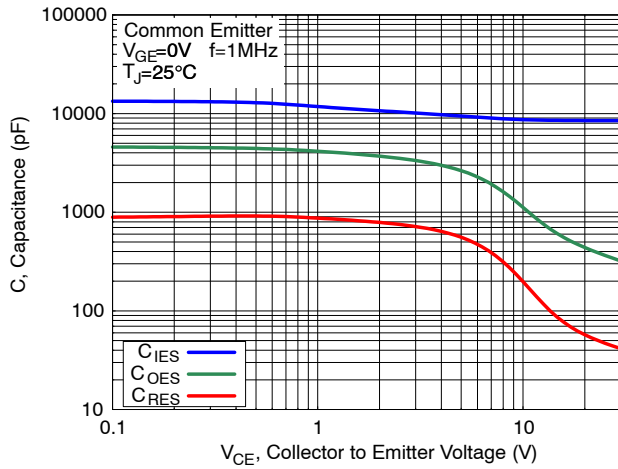


Figure 7. Capacitance Characteristics

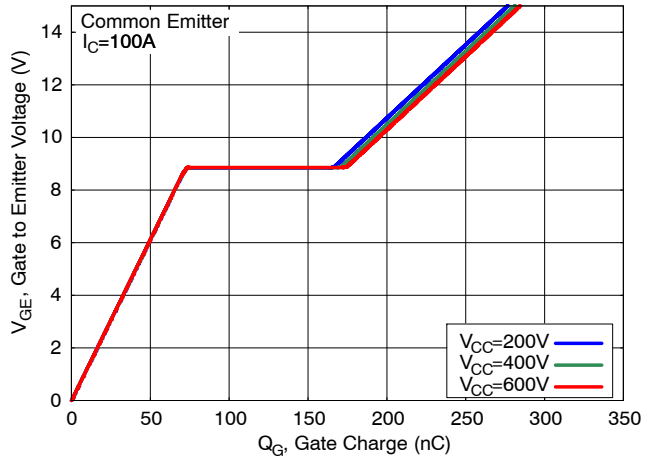


Figure 8. Gate Charge Characteristics

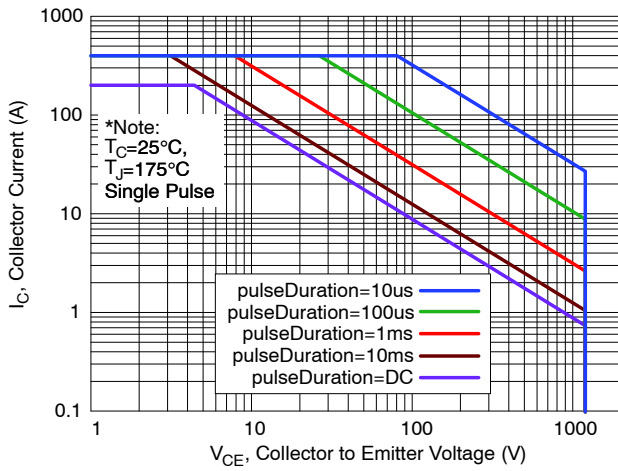


Figure 9. SOA Characteristics

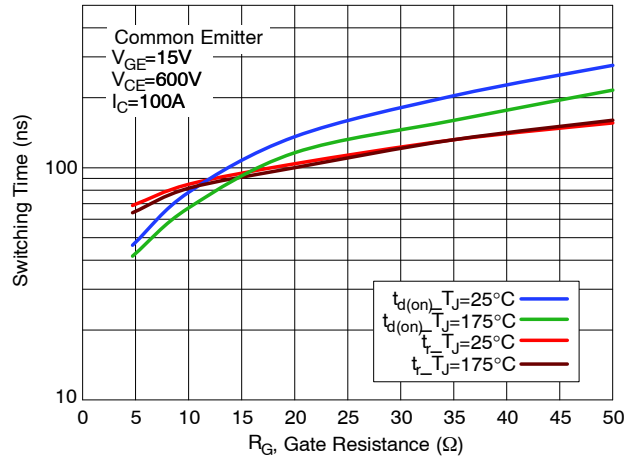


Figure 10. Turn-On Switching Time vs. Gate Resistance

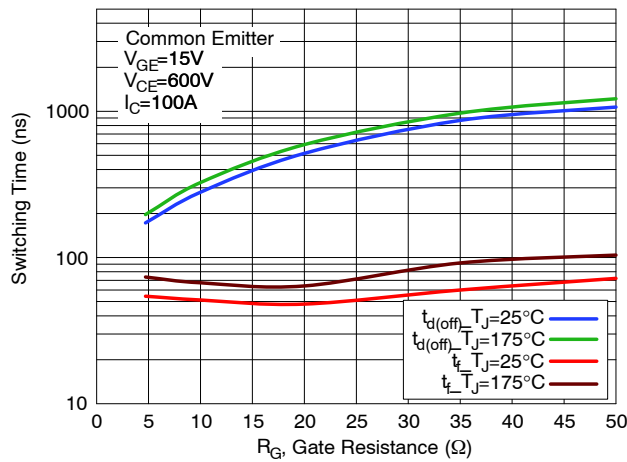


Figure 11. Turn-Off Switching Time vs. Gate Resistance

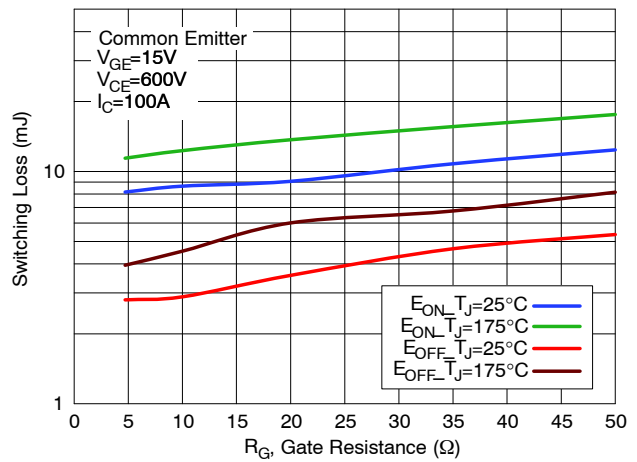
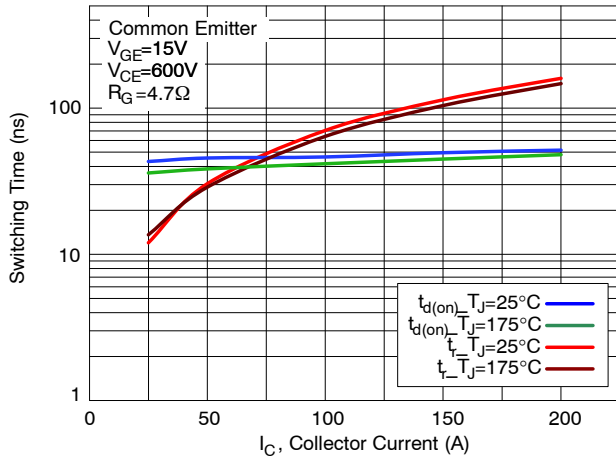


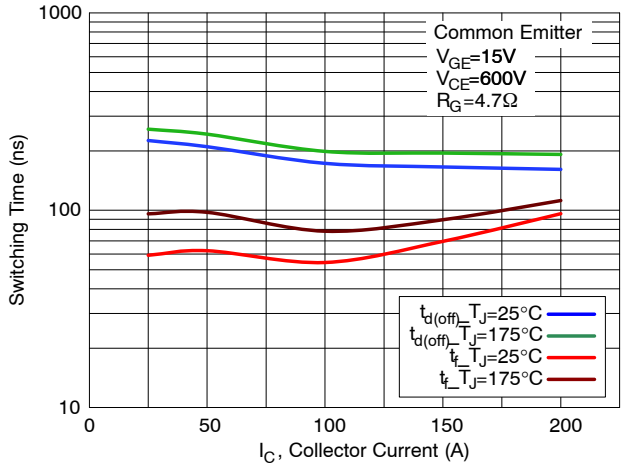
Figure 12. Switching Loss vs. Gate Resistance

# FGY100T120SWD

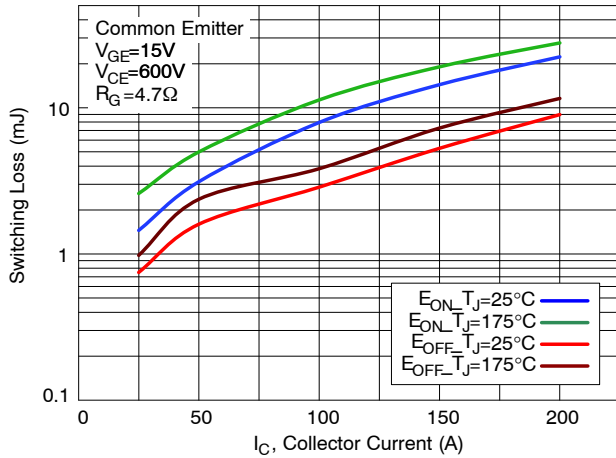
## TYPICAL CHARACTERISTICS



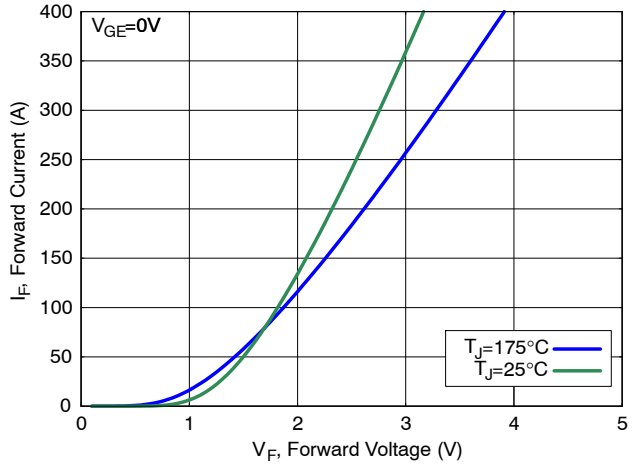
**Figure 13. Turn-On Switching Time vs. Collector Current**



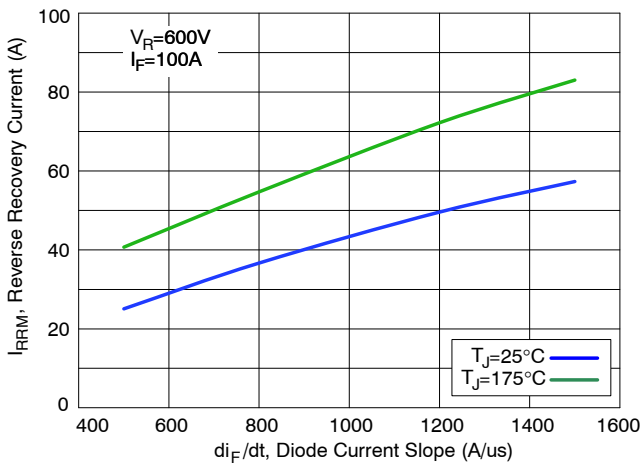
**Figure 14. Turn-Off Switching Time vs. Collector Current**



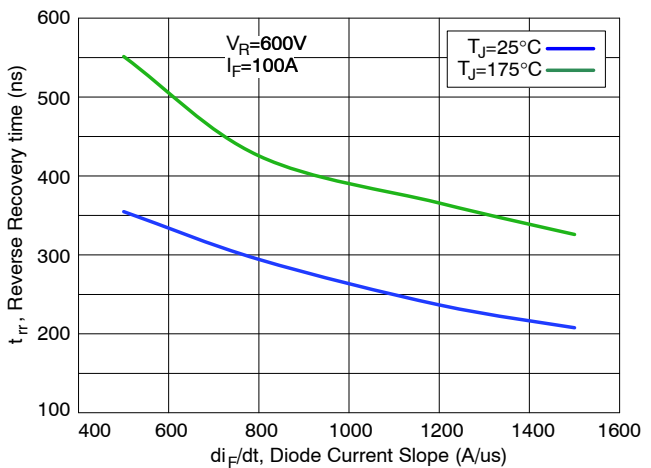
**Figure 15. Switching Loss vs. Collector Current**



**Figure 16. Diode Forward Characteristics**



**Figure 17. Diode Reverse Recovery Current**



**Figure 18. Diode Reverse Recovery Time**

# FGY100T120SWD

## TYPICAL CHARACTERISTICS

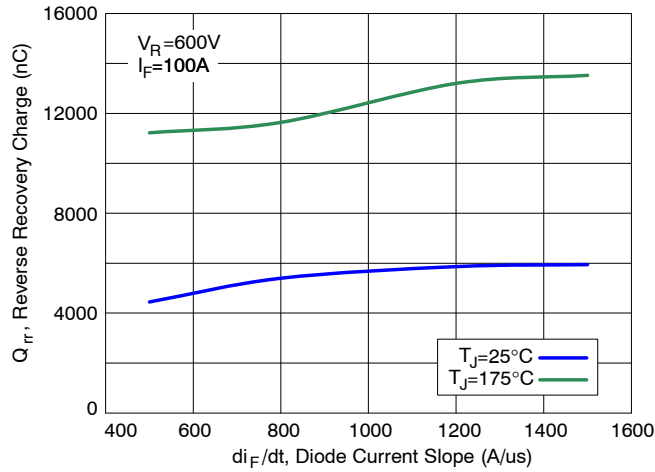


Figure 19. Diode Stored Charge Characteristics

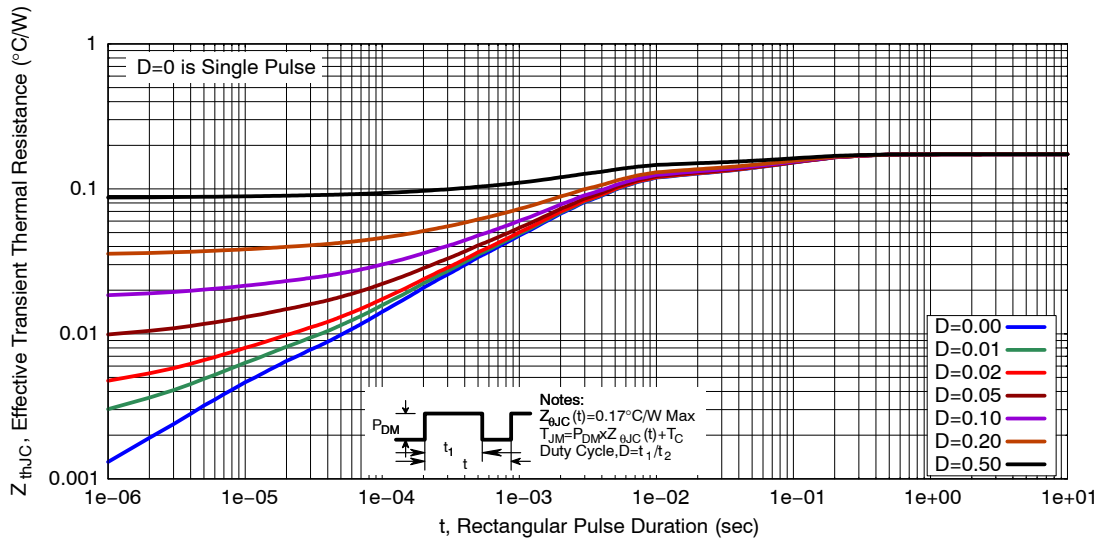


Figure 20. Transient Thermal Impedance of IGBT

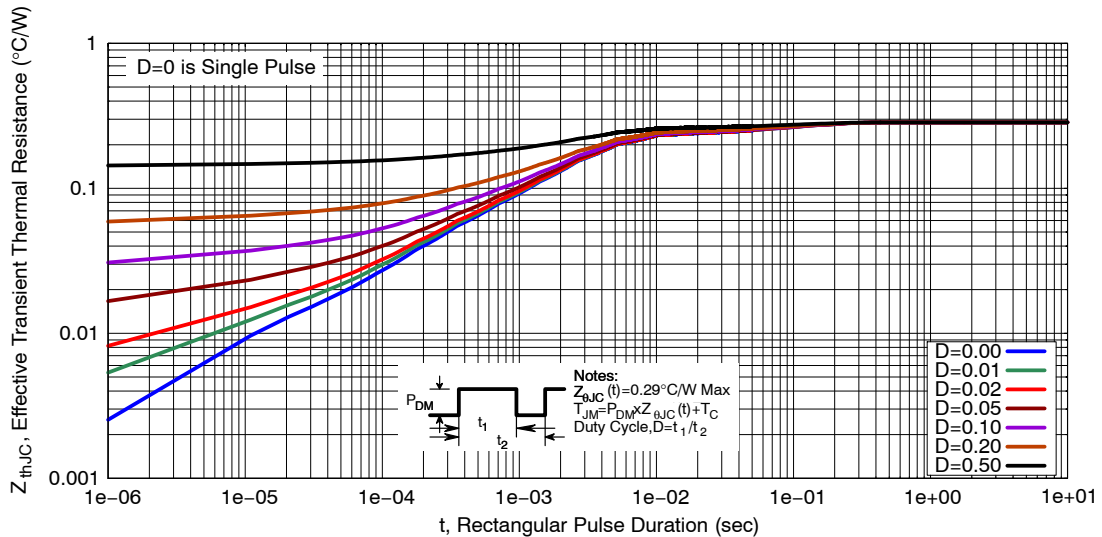
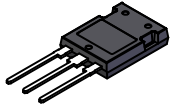


Figure 21. Transient Thermal Impedance of Diode

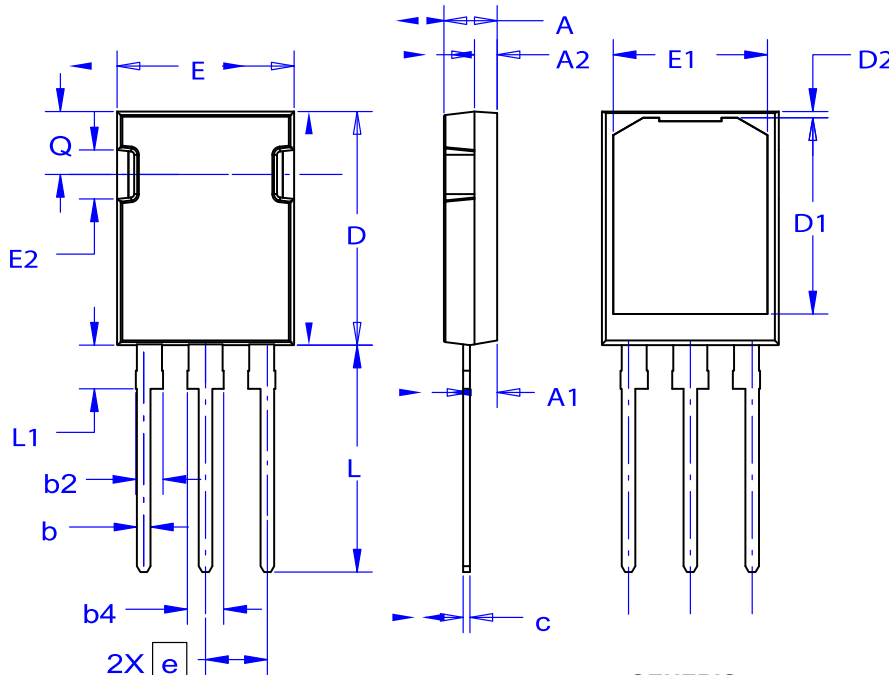


**TO-247-3LD**  
**CASE 340CD**  
**ISSUE A**

DATE 18 SEP 2018

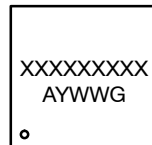
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- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.80	2.00	2.20
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.12	4.32	4.52
e	~	5.45	~
L	19.90	20.00	20.10
L1	3.69	3.81	3.93
Q	5.34	5.46	5.58
b	1.10	1.20	1.30
b2	2.10	2.24	2.39
b4	2.87	3.04	3.20
c	0.51	0.61	0.71
D1	16.63	16.83	17.03
D2	0.51	0.93	1.35
E1	13.40	13.60	13.80

**GENERIC MARKING DIAGRAM\***



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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